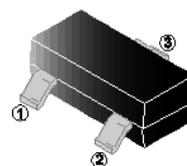


RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- High Density Cell Design for Low $R_{DS(ON)}$
- Voltage Controlled Small Signal Switch
- Moisture Sensitivity Level 1
- ESD Protected

SOT-23



APPLICATION

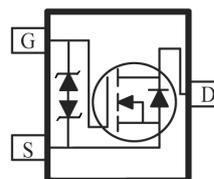
- Power Switching Application
- Uninterruptible Power Supply
- DC/DC Converter

MARKING

3099.

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-23	3K	7 inch



ORDER INFORMATION

Part Number	Type
SMS3099E-C	Lead (Pb)-free and Halogen-free

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current	I_D	$T_A=25^\circ\text{C}$	1.1
		$T_A=100^\circ\text{C}$	0.7
Pulsed Drain Current ¹	I_{DM}	3.3	A
Total Power Dissipation ²	P_D	$T_A=25^\circ\text{C}$	0.83
		$T_A=100^\circ\text{C}$	0.33
Thermal Resistance from Junction-Ambient ³	$R_{\theta JA}$	150	$^\circ\text{C/W}$
Operating Junction & Storage Temperature Range	T_J, T_{STG}	-55~150	$^\circ\text{C}$

Notes:

1. Repetitive rating; pulse width limited by max. Junction temperature.
2. P_D is based on max. Junction temperature, using junction-case thermal resistance.
3. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in the still air environment with $T_A=25^\circ\text{C}$. The maximum allowed junction temperature of 150 $^\circ\text{C}$. The value in any given application depends on the user's specific board design.

ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	30	-	-	V	$V_{GS}=0, I_D=250\mu\text{A}$	
Gate Threshold Voltage	$V_{GS(th)}$	0.5	1	1.5	V	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	
Gate-Body Leakage Current	I_{GSS}	-	-	± 10	μA	$V_{GS}= \pm 12\text{V}, V_{DS}=0$	
Zero Gate Voltage Drain Current	I_{DSS}	$T_J=25^\circ\text{C}$	-	-	1	μA	$V_{DS}=30\text{V}, V_{GS}=0$
		$T_J=150^\circ\text{C}$	-	-	100		
Drain-Source On-Resistance	$R_{DS(ON)}$		-	350	450	m Ω	$V_{GS}=10\text{V}, I_D=0.5\text{A}$
			-	430	550		$V_{GS}=4.5\text{V}, I_D=0.3\text{A}$
			-	640	850		$V_{GS}=2.5\text{V}, I_D=0.2\text{A}$
Gate resistance	R_G	-	90	-	Ω	$f=1\text{MHz}$	
Total Gate Charge	Q_g	-	1.85	-	nC	$V_{GS}=10\text{V}, V_{DS}=15\text{V}, I_D=1\text{A}$	
Gate-Source Charge	Q_{gs}	-	0.45	-			
Gate-Drain Charge	Q_{gd}	-	0.29	-			
Turn-on Delay Time	$t_{(on)}$	-	3	-			
Rise Time	t_r	-	19	-	nS	$V_{GS}=10\text{V}, V_{DD}=15\text{V}, I_D=1\text{A}$ $R_G=3\Omega$	
Turn-off Delay Time	$t_{(off)}$	-	17	-			
Fall Time	t_f	-	24	-			
Input Capacitance	C_{iss}	-	37	-	pF	$V_{DS}=15\text{V}$ $V_{GS}=0$ $f=1\text{MHz}$	
Output Capacitance	C_{oss}	-	10	-			
Reverse Transfer Capacitance	C_{rss}	-	5	-			
Source-Drain Diode							
Diode Forward Voltage	V_{SD}	-	0.9	1.2	V	$V_{GS}=0, I_S=0.5\text{A}$	
Maximum Body-Diode Continuous Current	I_S	-	-	1.1	A		
Reverse Recovery Time	T_{rr}	-	2	-	nS	$I_F=1\text{A}$	
Recovered Charge	Q_r	-	12	-	nC	$di/dt=100\text{A}/\mu\text{s}$	

TYPICAL CHARACTERISTICS

Figure 1. Output Characteristics

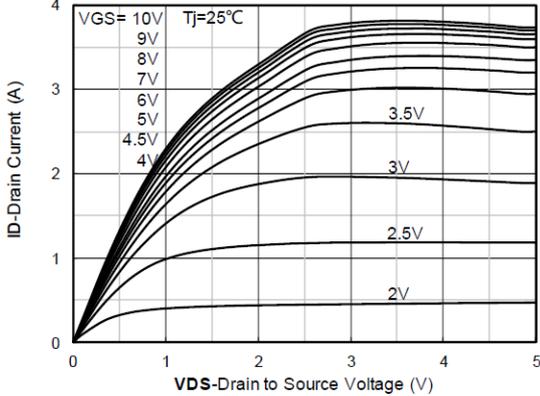


Figure 2. Transfer Characteristics

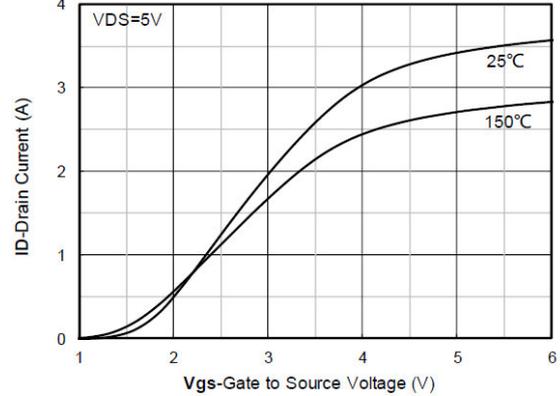


Figure 3. Capacitance Characteristics

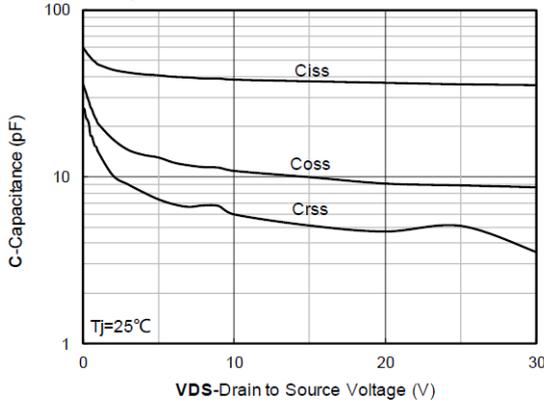


Figure 4. Gate Charge

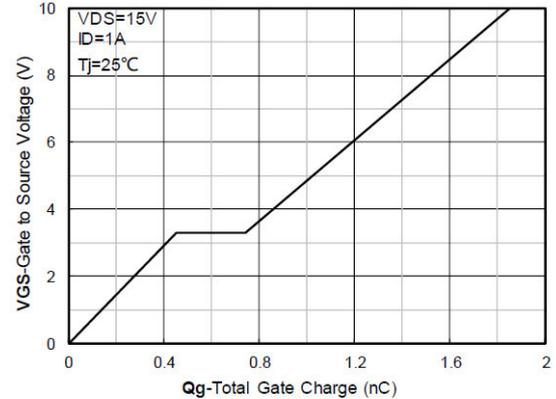


Figure 5. On-Resistance vs Gate to Source Voltage

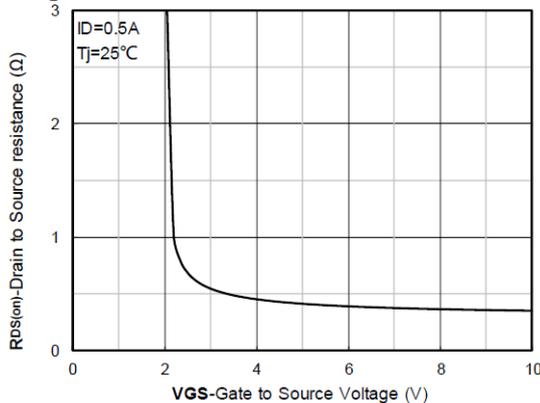


Figure 6. Normalized On-Resistance

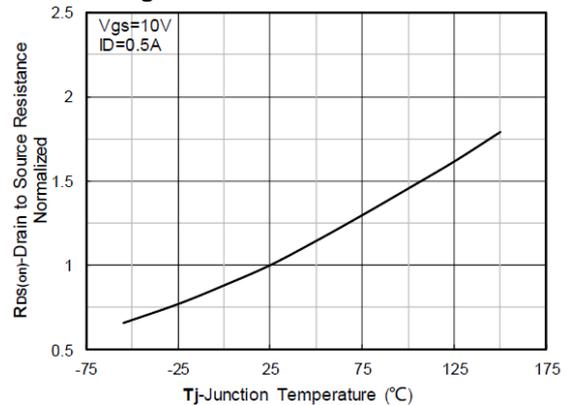


Figure 7. $R_{DS(on)}$ VS Drain Current

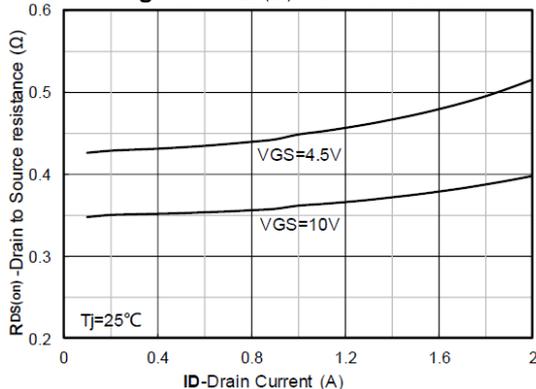
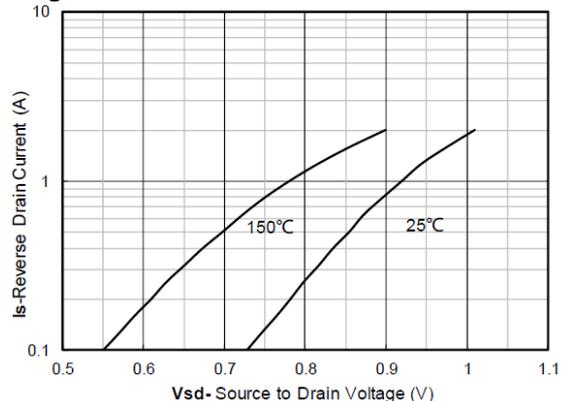


Figure 8. Forward Characteristics of Reverse Diode



TYPICAL CHARACTERISTICS

Figure 9. Normalized Breakdown Voltage

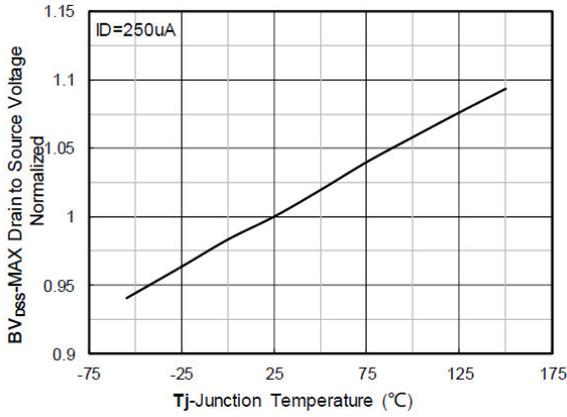


Figure 10. Normalized Threshold Voltage

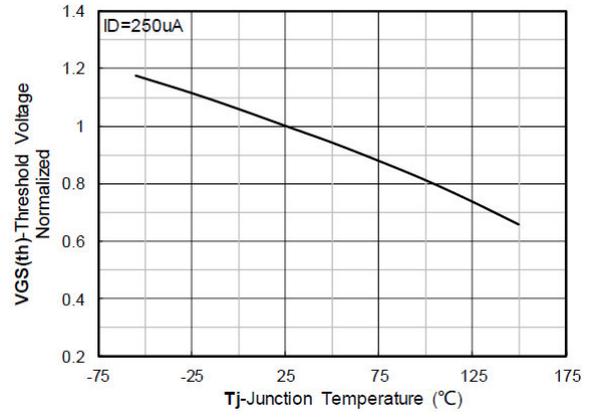


Figure 11. Current Dissipation

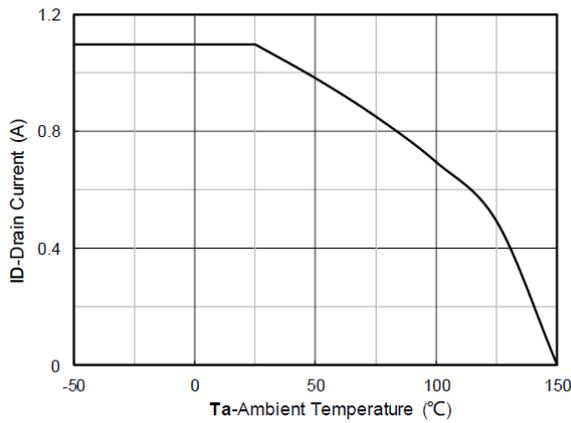


Figure 12. Power Dissipation

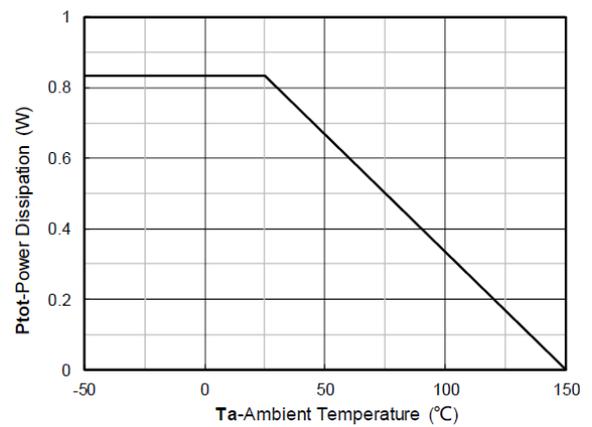


Figure 13. Maximum Transient Thermal Impedance

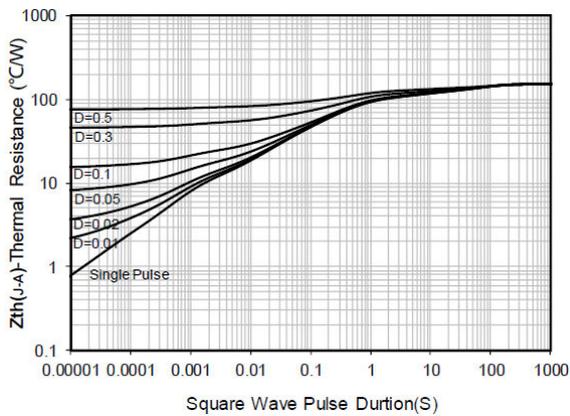
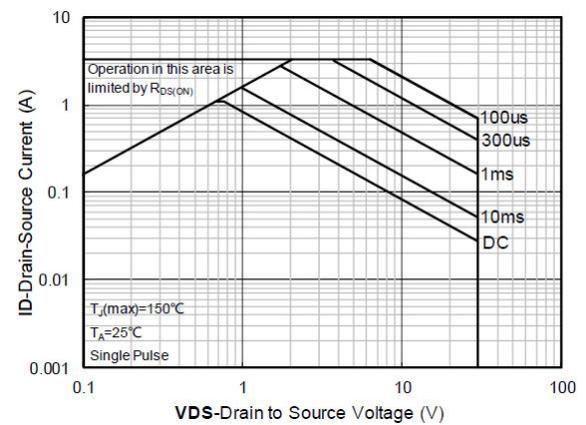
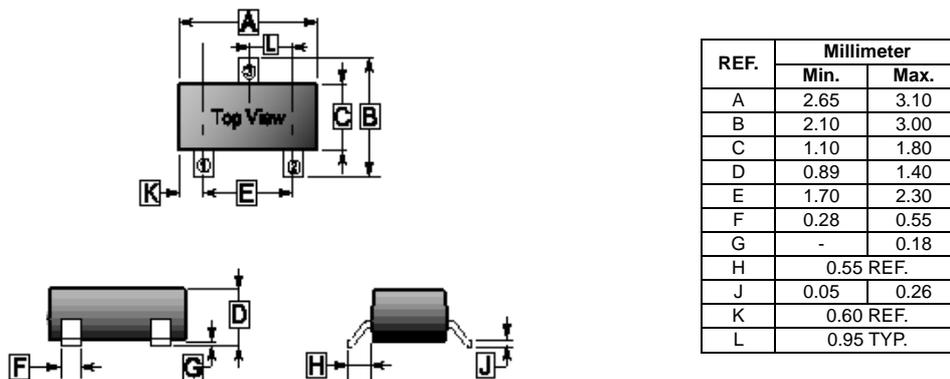


Figure 14. Safe Operation Area



PACKAGE OUTLINE DIMENSIONS

SOT-23



MOUNTING PAD LAYOUT

SOT-23

